TOSHIBA CMOS LINEAR INTEGRATED CIRCUIT SILICON MONOLITHIC

TC75W54FU, TC75W54FK

DUAL OPERATIONAL AMPLIFIER

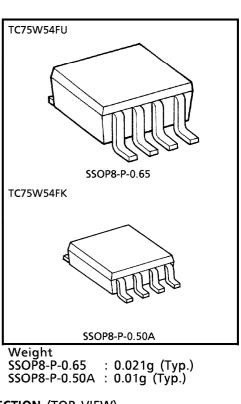
TC75W54 is a CMOS operational amplifier with low supply voltage, low supply current.

FEATURES

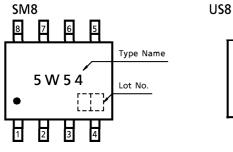
- Low supply voltage : $V_{DD} = \pm 0.9 \sim 3.5V$ or $1.8 \sim 7V$
- Low supply current : I_{DD} ($V_{DD} = 3V$) = 200 μ A (Typ.)
- The internally phase compensated operational amplifier.
- Small package

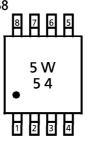
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	N
Supply Voltage	V _{DD} , V _{SS}	7	V
Differential Input Voltage	DVIN	±7	V
Input Voltage	VIN	V _{DD} ~V _{SS}	V
Power Dissipation	Pa	250 (SM8)	mW
	PD	200 (US8)	11174
Operating Temperature	T _{opr}	- 40~85	°C
Storage Temperature	T _{stg}	- 55~125	°C

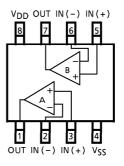


MARKING (TOP VIEW)





PIN CONNECTION (TOP VIEW)



980508EBA1
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ELECTRICAL CHARACTERISTICS

DC CHARACTERISTICS ($V_{DD} = 3.0V$, $V_{SS} = GND$, $Ta = 25^{\circ}C$)

CHARACTERISTIC	SYMBOL	TEST CIR- CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Input Offset Voltage	VIO	1	$R_{S} = 1k\Omega$	—	2	10	mV
Input Offset Current	lio	_	—	—	1	—	pА
Input Bias Current	Ц	_	—	—	1	—	pА
Common Mode Input Voltage	CMV _{IN}	2	—	0.0	—	2.1	V
Voltage Gain (Open Loop)	GV	_	—	60	70	—	dB
Maximum Output Voltage	∨он	3	$R_L \ge 100 k\Omega$	2.9		_	v
Maximum Output Voltage	VOL	4	$R_{L} \ge 100 k\Omega$	—		0.1	v
Common Mode Input Signal Rejection Ratio	CMRR	2	V _{IN} = 0.0~2.1V	60	70	_	dB
Supply Voltage Rejection Ratio	SVRR	1	V _{DD} = 1.8~7.0V	60	70	_	dB
Supply Current	I _{DD}	5	_	_	200	400	μA
Source Current	I _{source}	6	_	100	200	_	μA
Sink Current	l _{sink}	7		200	700	_	μA

DC CHARACTERISTICS ($V_{DD} = 1.8V$, $V_{SS} = GND$, $Ta = 25^{\circ}C$)

CHARACTERISTIC	SYMBOL	TEST CIR- CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Input Offset Voltage	VIO	1	$R_S = 10k\Omega$	—	2	10	mV
Input Offset Current	li0	_	—	_	1	_	pА
Input Bias Current	Ц	_	—	—	1	_	pА
Common Mode Input Voltage	CMVIN	2	—	0.2	—	0.9	V
Voltage Gain (Open Loop)	GV	_		60	70	—	dB
Maximum Output Voltage	Vон	3	$R_L \ge 100 k\Omega$	1.7	_	_	v
	VOL	4	$R_L \ge 100 k\Omega$	—	—	0.1	v
Supply Current	IDD	5	—	—	160	320	μA
Source Current	lsource	6	—	80	160	_	μA
Sink Current	l _{sink}	7	_	200	600	_	μA

AC CHARACTERISTICS ($V_{DD} = 3.0V$, $V_{SS} = GND$, $Ta = 25^{\circ}C$)

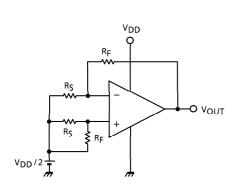
CHARACTERISTIC	SYMBOL	TEST CIR- CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Slew Rate	SR	—	—	_	0.7	—	V/μs
Unity Gain Cross Frequency	fŢ	—	—	_	0.9	—	MHz

AC CHARACTERISTICS ($V_{DD} = 1.8V$, $V_{SS} = GND$, $Ta = 25^{\circ}C$)

CHARACTERISTIC	SYMBOL	TEST CIR- CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Slew Rate	SR	Ι	—	_	0.6	_	V/µs
Unity Gain Cross Frequency	fT	—	_	_	0.8	—	MHz

TEST CIRCUIT

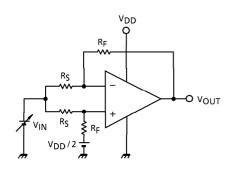
1. SVRR, VIO



• SVRR $V_{DD} = 1.8V : V_{DD} = V_{DD}1, V_{OUT} = V_{OUT}1$ $V_{DD} = 7.0V : V_{DD} = V_{DD}2, V_{OUT} = V_{OUT}2$ $SVRR = 20 \log \left(\left| \frac{V_{OUT}1 - V_{OUT}2}{V_{DD}1 - V_{DD}2} \right| \times \frac{R_S}{R_F + R_S} \right)$

•
$$V_{IO} = \left(V_{OUT} - \frac{V_{DD}}{2} \right) \times \frac{R_S}{R_F + R_S}$$

2. CMRR, CMV_{IN}



• CMRR

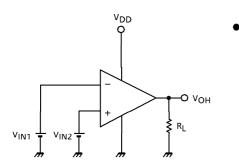
$$V_{IN} = 0.0V : V_{IN} = V_{IN}1, V_{OUT} = V_{OUT}1$$

$$V_{IN} = 2.1V : V_{IN} = V_{IN}2, V_{OUT} = V_{OUT}2$$

$$CMRR = 20 log \left(\left| \frac{V_{OUT}1 - V_{OUT}2}{V_{IN}1 - V_{IN}2} \right| \times \frac{R_S}{R_F + R_S} \right)$$

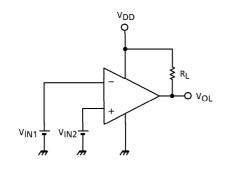
CMV_{IN}

3. V_{OH}



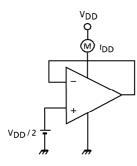
 V_{OH} $V_{IN1} = \frac{V_{DD}}{2} - 0.05V$ $V_{IN2} = \frac{V_{DD}}{2} + 0.05V$

4. V_{OL}

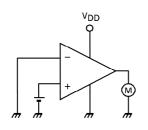


• V_{OL}
V_{IN1} =
$$\frac{V_{DD}}{2}$$
 + 0.05V
V_{IN2} = $\frac{V_{DD}}{2}$ - 0.05V

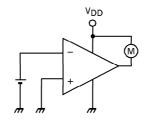
5. I_{DD}

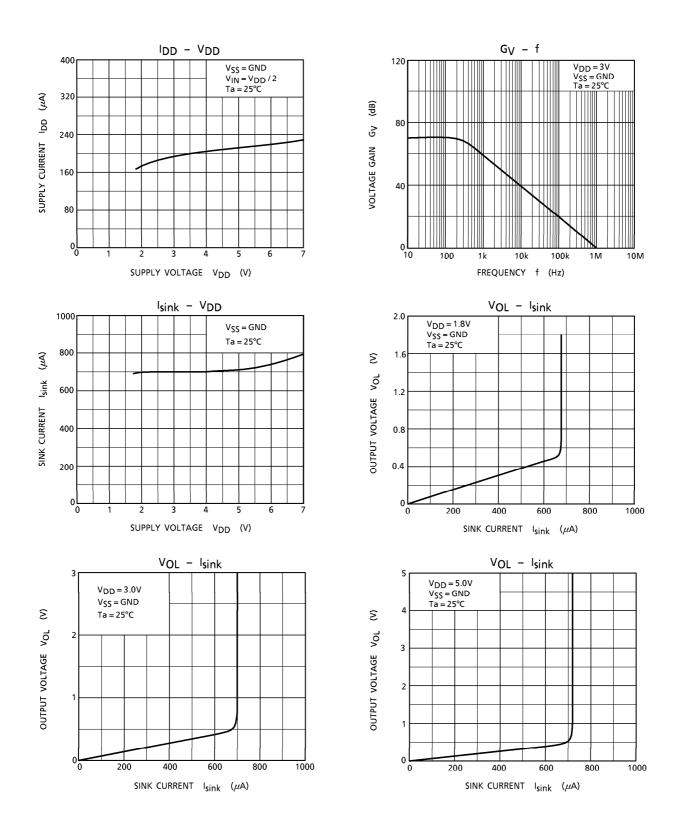


6. I_{source}

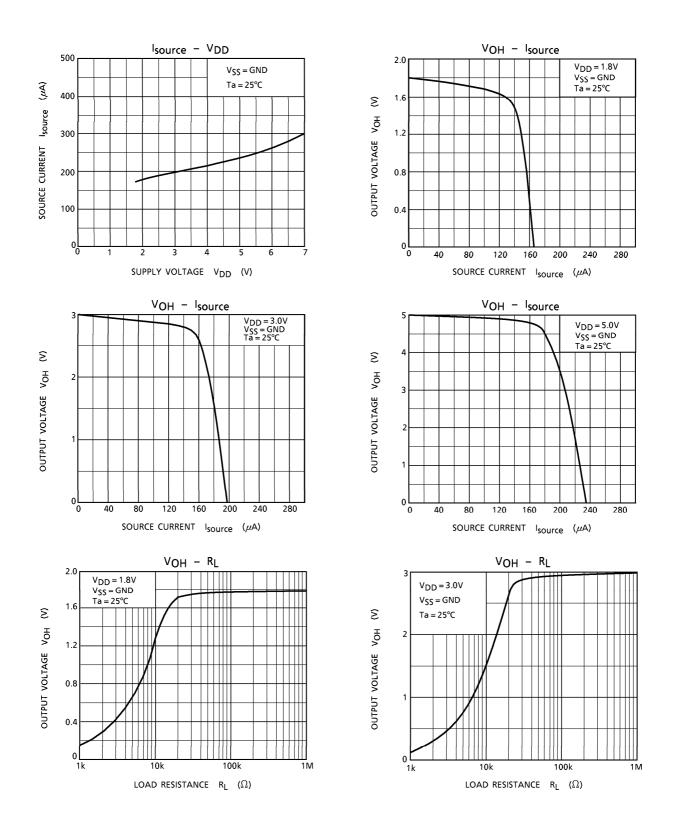


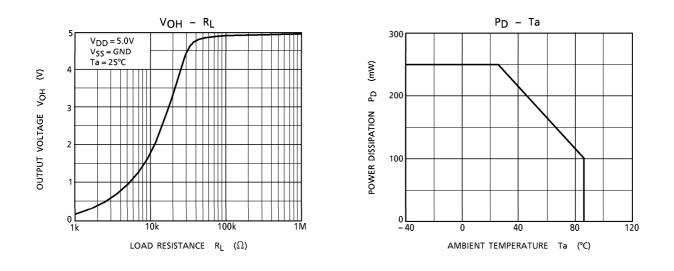






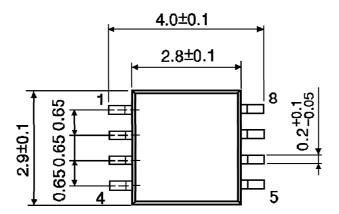
<u>TOSHIBA</u>

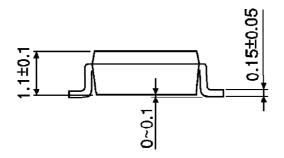




OUTLINE DRAWING SSOP8-P-0.65

Unit : mm

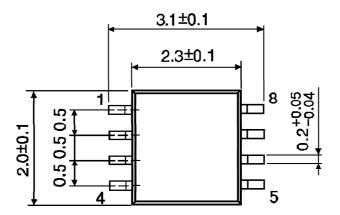


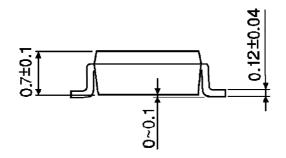


Weight : 0.021g (Typ.)

OUTLINE DRAWING SSOP8-P-0.50A

Unit : mm





Weight : 0.01g (Typ.)

单击下面可查看定价,库存,交付和生命周期等信息

>>Toshiba(东芝)